

IXTH152N085T-VB Datasheet

N-Channel 80 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω) MAX.	I_D (A)	Q_g (TYP.)
80	0.0028 at $V_{GS} = 10$ V	215	94
	0.0030 at $V_{GS} = 7.5$ V	205	

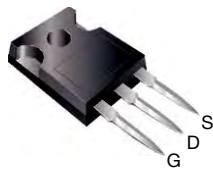
FEATURES

- Trench power MOSFET
- Maximum 175 °C junction temperature
- Very low Q_{gd} reduces power loss from passing through $V_{plateau}$
- 100 % R_g and UIS tested

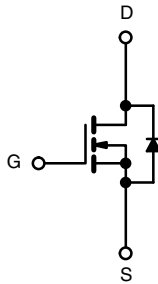


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TO-247AC



Top View



N-Channel MOSFET

APPLICATIONS

- Power supply
- Secondary synchronous rectification
- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- Battery management

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	A
		$T_C = 70$ °C	
Pulsed Drain Current ($t = 100$ μ s)	I_{DM}	600	
Avalanche Current	I_{AS}	70	
Single Avalanche Energy ^a	E_{AS}	245	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	W
		$T_C = 125$ °C	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.4	

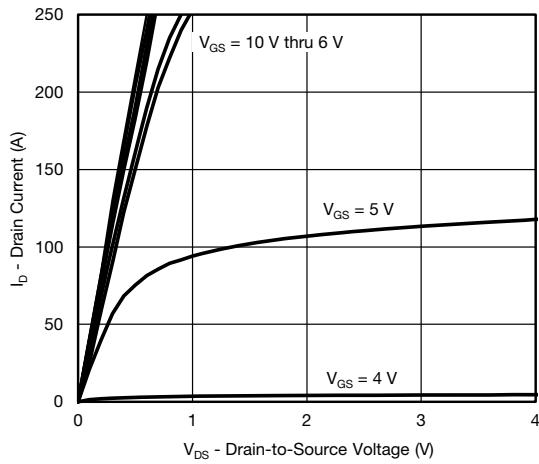
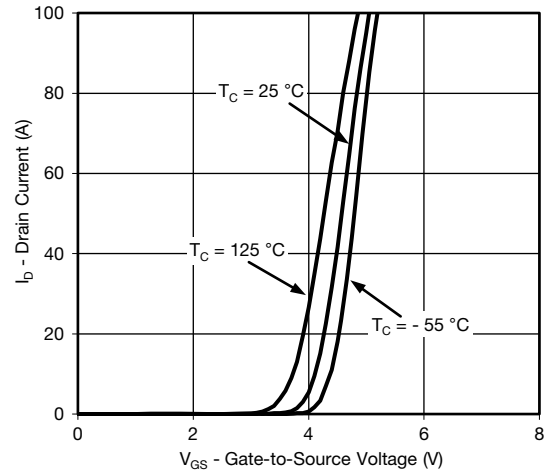
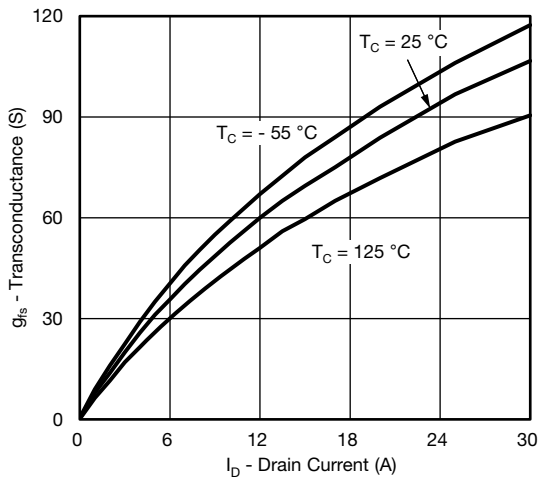
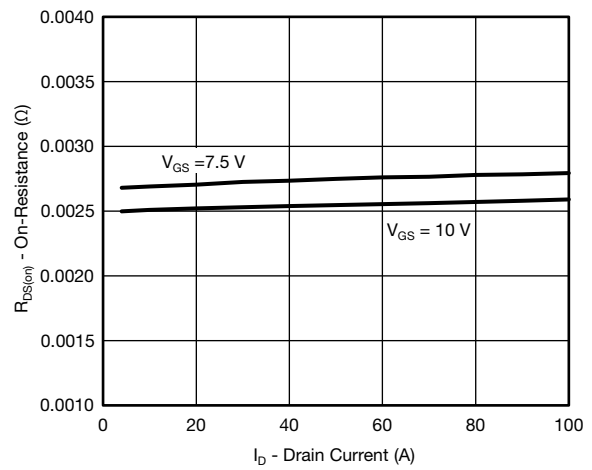
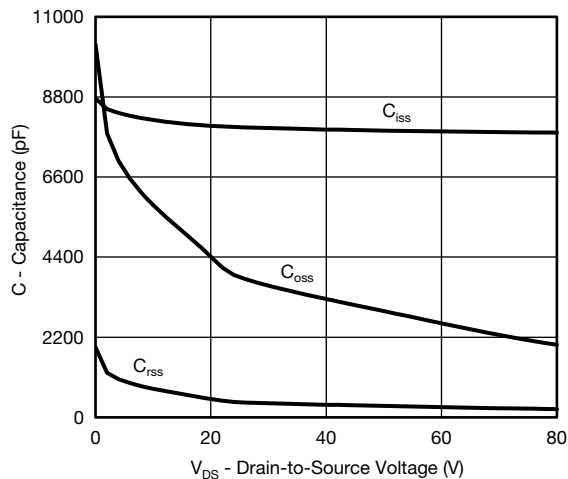
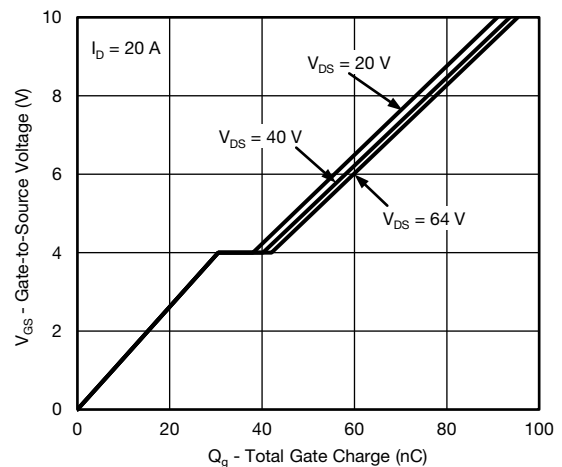
Notes

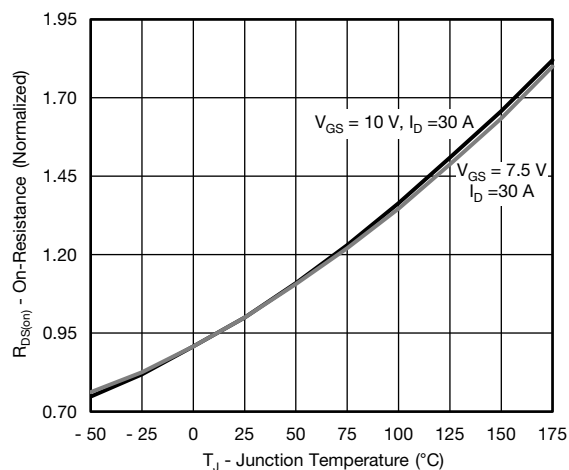
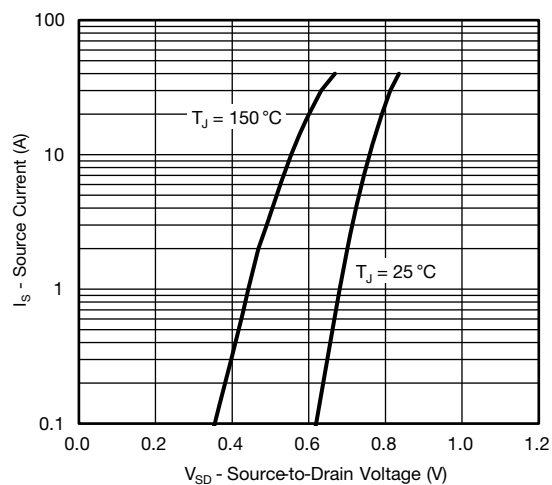
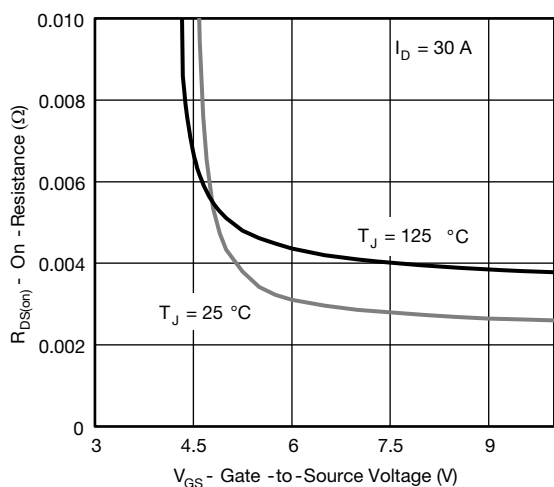
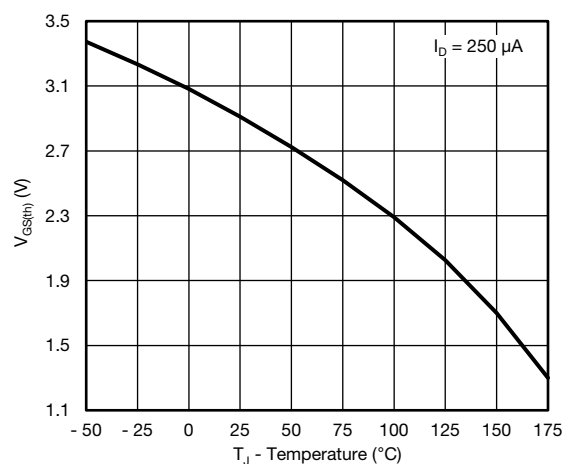
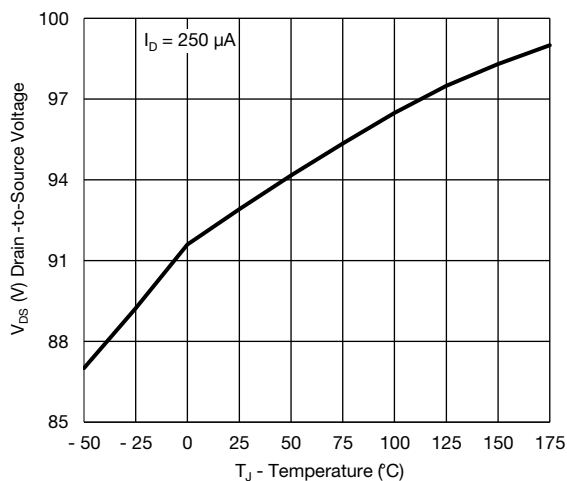
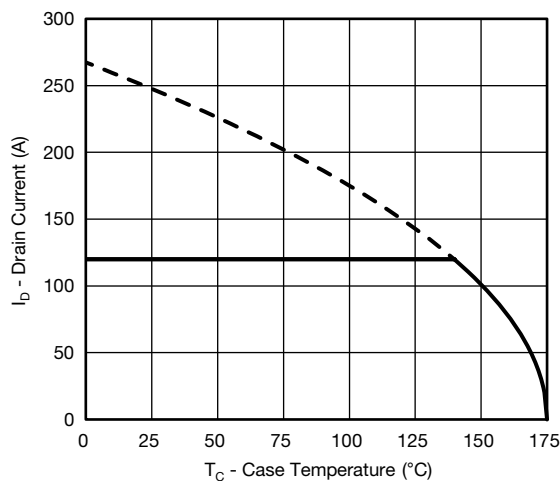
- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).
- Package limited.

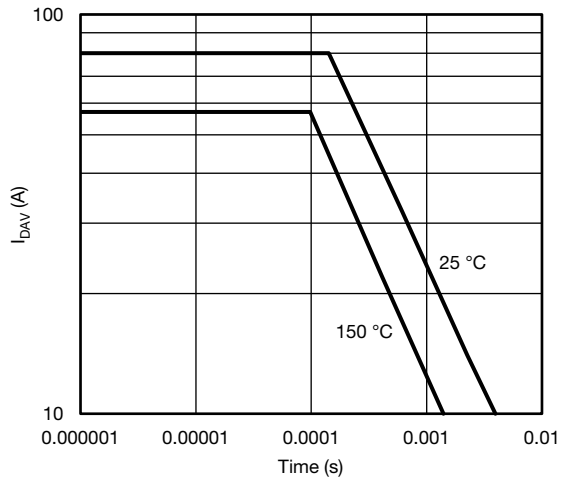
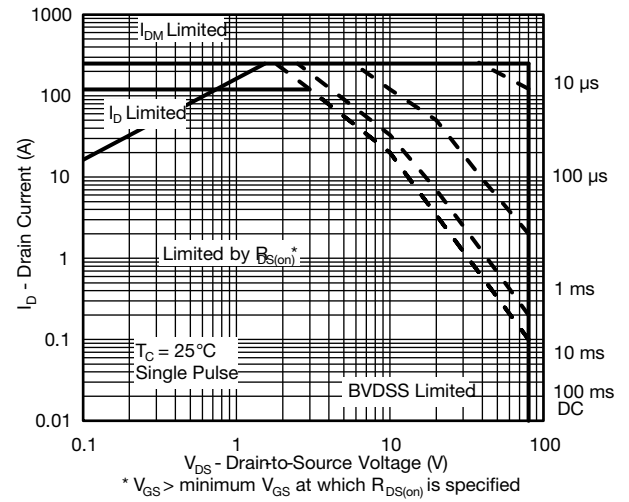
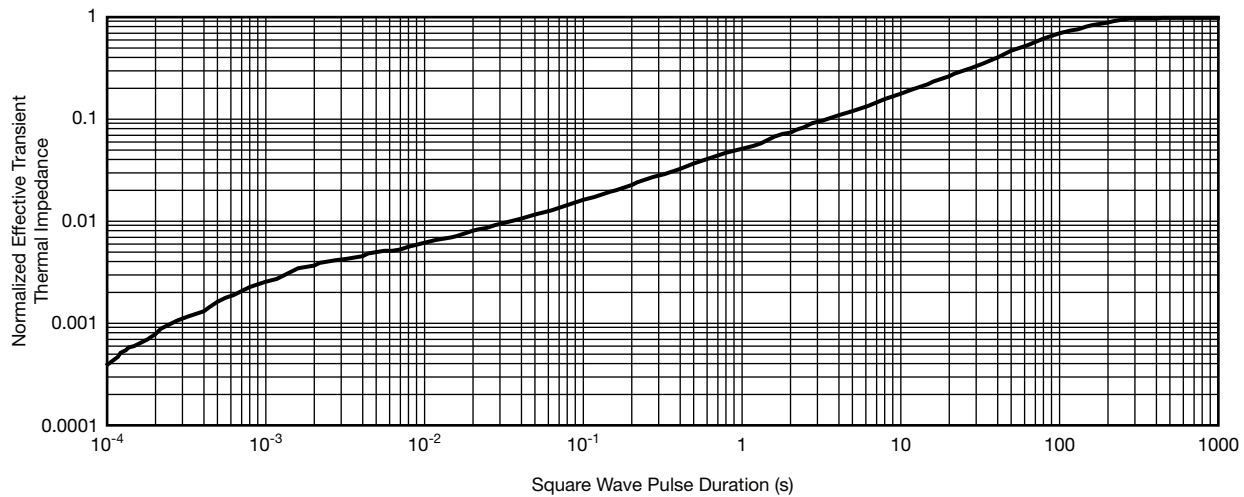
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	80	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2	-	4	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 250	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 125 °C	-	-	150	
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 175 °C	-	-	5	mA
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	120	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A	-	0.0028	-	Ω
		V _{GS} = 7.5 V, I _D = 20 A	-	0.0030	-	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	-	82	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 40 V, f = 1 MHz	-	7910	-	pF
Output Capacitance	C _{oss}		-	3250	-	
Reverse Transfer Capacitance	C _{rss}		-	348	-	
Total Gate Charge ^c	Q _g	V _{DS} = 40 V, V _{GS} = 10 V, I _D = 20 A	-	94	141	nC
Gate-Source Charge ^c	Q _{gs}		-	31	-	
Gate-Drain Charge ^c	Q _{gd}		-	10	-	
Gate Resistance	R _g	f = 1 MHz	0.28	1.4	2.8	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 40 V, R _L = 4 Ω I _D ≡ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	-	24	40	ns
Rise Time ^c	t _r		-	24	40	
Turn-Off Delay Time ^c	t _{d(off)}		-	34	60	
Fall Time ^c	t _f		-	14	28	
Drain-Source Body Diode Ratings and Characteristics ^b (T _C = 25 °C)						
Pulsed Current (t = 100 μs)	I _{SM}		-	-	250	A
Forward Voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V	-	0.8	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 34 A, di/dt = 100 A/μs	-	126	190	ns
Peak Reverse Recovery Charge	I _{RM(REC)}		-	5	10	A
Reverse Recovery Charge	Q _{rr}		-	0.315	0.475	μC

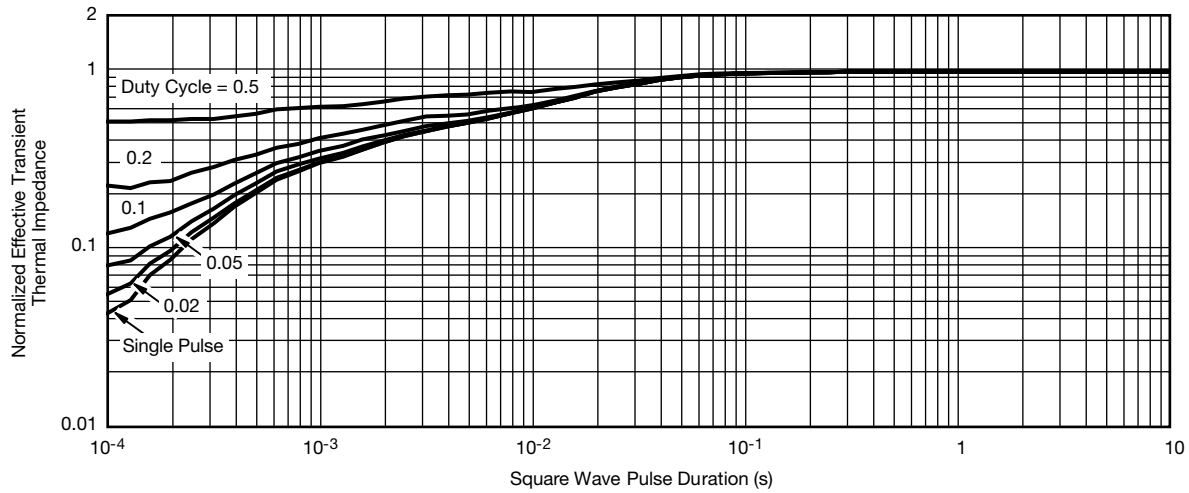
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Drain Source Breakdown vs. Junction Temperature

Current De-rating

THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Single Pulse Avalanche Current Capability vs. Time

Safe Operating Area

Normalized Thermal Transient Impedance, Junction-to-Ambient

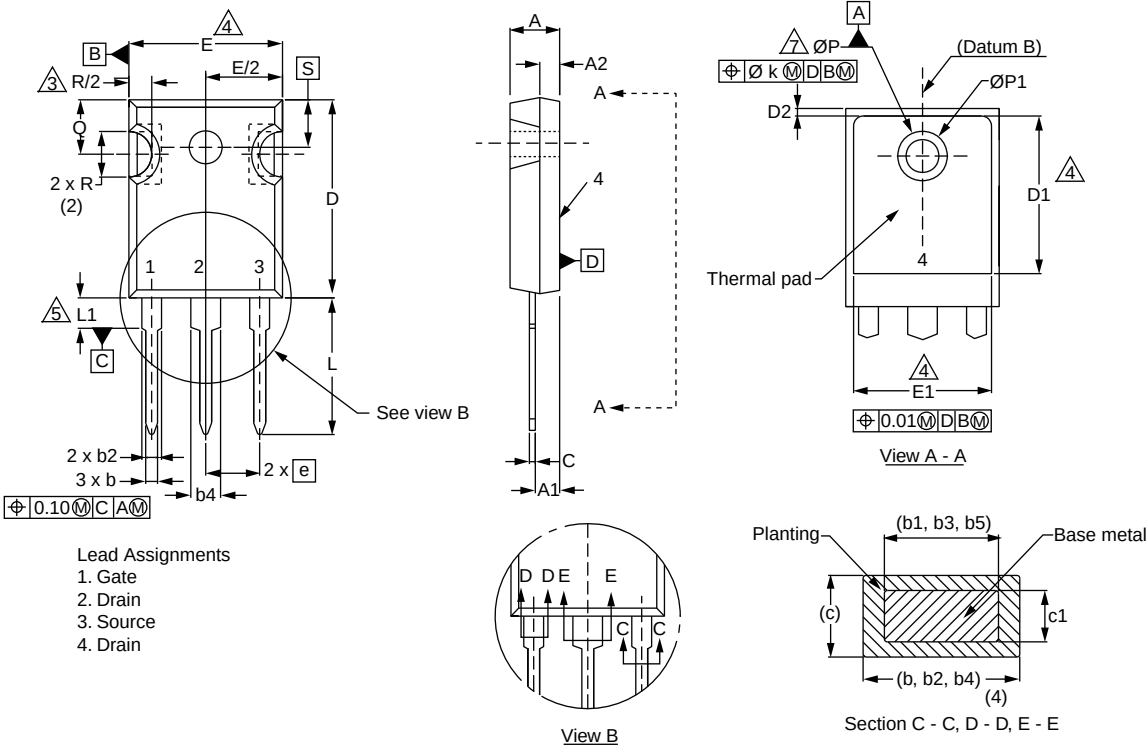
THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^{\circ}\text{C}$)
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-247AC



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.58	5.31	0.180	0.209
A1	2.21	2.59	0.087	0.102
A2	1.17	2.49	0.046	0.098
b	0.99	1.40	0.039	0.055
b1	0.99	1.35	0.039	0.053
b2	1.53	2.39	0.060	0.094
b3	1.65	2.37	0.065	0.093
b4	2.42	3.43	0.095	0.135
b5	2.59	3.38	0.102	0.133
c	0.38	0.86	0.015	0.034
c1	0.38	0.76	0.015	0.030
D	19.71	20.82	0.776	0.820
D1	13.08	-	0.515	-

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D2	0.51	1.30	0.020	0.051
E	15.29	15.87	0.602	0.625
E1	13.72	-	0.540	-
e	5.46 BSC		0.215 BSC	
Ø k	0.254		0.010	
L	14.20	16.25	0.559	0.640
L1	3.71	4.29	0.146	0.169
N	7.62 BSC		0.300 BSC	
Ø P	3.51	3.66	0.138	0.144
Ø P1	-	7.39	-	0.291
Q	5.31	5.69	0.209	0.224
R	4.52	5.49	0.178	0.216
S	5.51 BSC		0.217 BSC	

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